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customized optoelectronics



Product Data Sheet

LED Chip vis

EOLC-515-34

Rev. 01 aus 2011

Radiation	Type	Electrodes
green		P + N up

	<p>Description</p> <ul style="list-style-type: none"> -Substrate: Sapphire, epitaxial layer: GaN based Material -N bonding pad electrode: Au alloy -P bonding pad electrode: Au alloy <p><i>Above drawing is not on real scale.</i></p>
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Maximum Ratings

$T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward current (DC)		I_F			20	mA
Peak forward current	$t_p \leq 50 \mu\text{s}$,	I_{FM}			100	mA

Optical and Electrical Characteristics

$T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 20\text{mA}$	V_F		3.3	3.5	V
Reverse current	$V_R = 5\text{V}$	I_R			1	μA
Dominant wavelength	$I_F = 20\text{mA}$	λ_p	512	515	518	nm
Full width at half maximum	$I_F = 20\text{mA}$	$\Delta\lambda$		40		nm
Luminous intensity ¹	$I_F = 20\text{mA}$	I_v	400		550	mcd

Packing

Chips on adhesive film with wire-bond side top